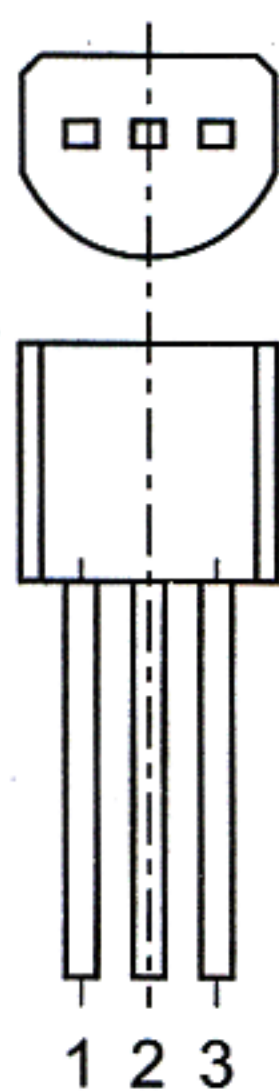


TO-92 Plastic-Encapsulate Transistors

PCR 0.6A SILICON PLANAR PNP THYRISTOR



TO-92

1. CATHODE

2. GATE

3. ANODE

FEATURES

CURRENT- I_{GT} : 120 μ A

I_{TRMS} : 0.6 A

V_{DRM} : 400 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to + 150°C

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol		Test conditions	MIN	MAX	UNIT
On state voltage	V_{TM}		$I_{TM}=0.6\text{ A}$		1.7	V
Gate trigger voltage	V_{GTF}		$V_{AK}=7\text{ V}$		0.8	V
Repetitive peak off-state voltage	V_{DRM}		$I_{DRM}=10\text{ }\mu\text{ A}$, $V_{MAX}=1010\text{ V}$	400		V
Holding current	I_H		$I_{HL}=20\text{ mA}$, $A_v=7\text{ V}$		5	mA
Gate trigger current	I_{GTF}	A2	$V_{AR}=7\text{ V}$	5	15	$\mu\text{ A}$
		A1		15	30	$\mu\text{ A}$
		A-1		30	45	$\mu\text{ A}$
		A-2		45	60	$\mu\text{ A}$
		A		60	80	$\mu\text{ A}$
		B		80	120	$\mu\text{ A}$